

Linear RF Amplifier

- **Frequency Response: 225-400 MHz**
- **Linear Power: 10 watt**
- **Saturated Power: 20 watts**
- **Gain: 15 dB**



Description:

Designed for linear application in the 225 to 400 MHz range. This amplifier utilizes class AB RF Power MOSFET devices that provide high gain, wide dynamic range and an excellent 3rd order intercept point. Suggested applications: multi-carrier, pulse, AM & FM modulation.

ELECTRICAL SPECIFICATION @ VDD= +24VDC: Temp.=25°C, 50Ω System

Parameter	Symbol	Min	Typ	Max	Unit
Operating Frequency	BW	225		400	MHz
Power Output Saturated	P _{sat}		20		Watt
Power Output P-1dB	P _{-1dB}	13	15		Watt
Gain	G	13	15		dB
Small Signal Gain Flatness	ΔG			±0.5	dB
Input VSWR	S11		1.4:1	1.5:1	-
Harmonics	H		-23	-20	dBc
Inter-modulation Point 2 Tones, 2W per tone @ 350 & 351MHz	IP ₃		+52		dBm
Spurious Signals	dBc		-70	-60	dBc
Operating Voltage	Vdc	22	24	28	Volt
Operating Current	Amps		1.6	2	Amp
Enable / Disable (shut down pin: gnd=off, open=on)	ms	Not Included			ms

MECHANICAL SPECIFICATION

Parameter	Description	Limits	Units
Dimensions	2.2 x 4 x 0.86	Max	Inch
RF Connectors IN/OUT	SMA	-	-
DC Connectors	Filtered feed-through	-	-
Cooling	Heat-sink not included	-	-
Weight		Max	lb

PROTECTIONS

Thermal Shutdown	Bi-metal switch set at 70°C with self reset.	Typ
Input Overdrive	+28 dBm Max	Max
Load VSWR	6.0:1 up to 10 Watts	Max
Reverse Polarity Protection	None	-

ENVIRONMENTAL CHARACTERISTICS

Parameter	Symbol	Min	Typ	Max	Units
Operating Case Temperature	Tc	0°C		+50°C	°C
Storage Temperature	Tstg	-30°C		+100°C	°C
Relative humidity non-condensation	RH	95			%

Outline Drawing

